



DMT6017LDV

65V N-CHANNEL ENHANCEMENT MODE MOSFET

PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	$22m\Omega @ V_{GS} = 10V$	25.3A
65V	29mΩ @ V _{GS} = 4.5V	22.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

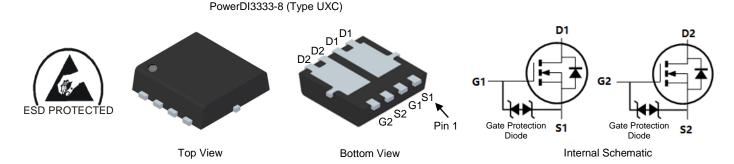
- Wireless Charging
- DC-DC Converters
- Power Management

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

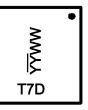
	Part Number	Case	Packaging		
DMT6017LDV-7		PowerDI3333-8 (Type UXC)	2,000/Tape & Reel		
DMT6017LDV-13		PowerDI3333-8 (Type UXC)	3,000/Tape & Reel		
Notes: 1 No purposely added lead Fully FU Directive 2002/95/FC (RoHS) 2011/65/FU (RoHS 2) & 2015/863/FU (RoHS 3) compliant					

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{T7D}{YY} = Product Type Marking Code$ $\frac{YY}{YY} = Date Code Marking$ $\frac{YY}{Y} = Last Two Digits of Year (ex: 19 = 2019)$ WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	65	V	
Gate-Source Voltage	V _{GSS}	±16	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$	T _C = +25°C T _C = +70°C	ID	25.3 20.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	100	А	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	25	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	100	A	
Avalanche Current, L = 0.1mH	I _{AS}	19	A	
Avalanche Energy, L = 0.1mH	E _{AS}	18	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	0.98	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ extsf{ heta}JA}$	127.9	°C/W	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.34	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta}JA$	53.5	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	5.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

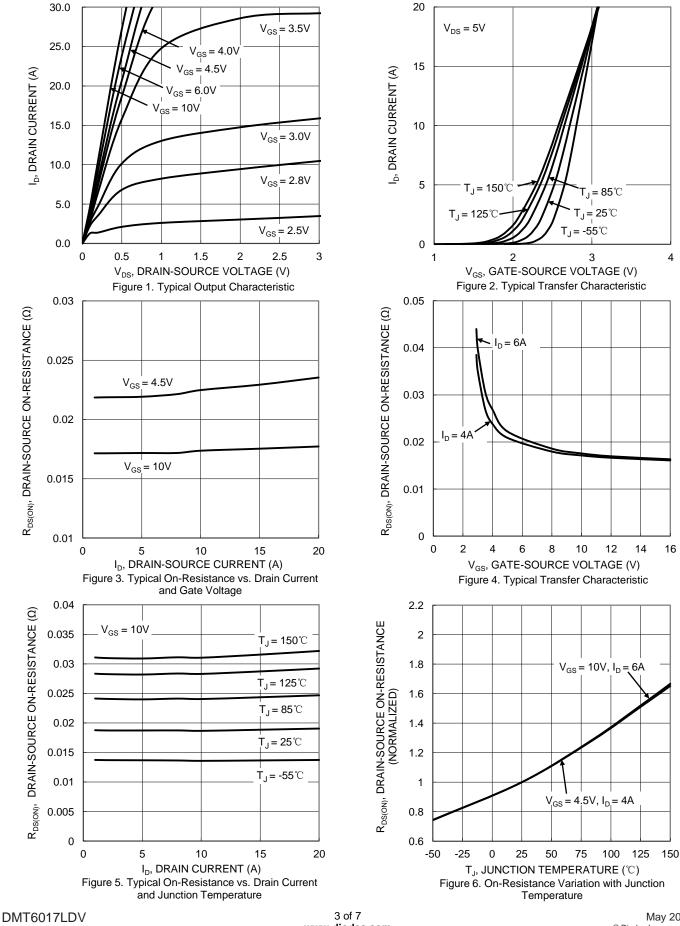
			_				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	65	—	_	V	$V_{GS} = 0V, I_D = 10mA$	
Zero Gate Voltage Drain Current	I _{DSS}		—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		-	±10	μA	$V_{GS} = \pm 12.8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	—	2.3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	р		17.5	22	mΩ	$V_{GS} = 10V, I_D = 6A$	
	R _{DS(ON)}		22.3	29	11122	$V_{GS} = 4.5V, I_D = 4A$	
Diode Forward Voltage	V _{SD}	_	0.7	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		891	_	pF		
Output Capacitance	Coss		223	—	pF	− V _{DS} = 30V, V _{GS} = 0V, − f = 1MHz	
Reverse Transfer Capacitance	Crss	_	29	_	pF		
Gate Resistance	Rg	_	1.57	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	7.5	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg		15.3	—	nC		
Gate-Source Charge	Q _{gs}	_	1.8	_	nC	$V_{DS} = 30V, I_D = 6A$	
Gate-Drain Charge	Q _{gd}	_	3.1	_	nC	-	
Turn-On Delay Time	t _{D(ON)}	_	4.0	_	ns	V _{GS} = 10V, V _{DS} = 30V,	
Turn-On Rise Time	t _R	_	5.9	_	ns		
Turn-Off Delay Time	t _{D(OFF)}		11.7	_	ns	$R_g = 3.3\Omega, I_D = 6A$	
Turn-Off Fall Time	t _F		3.3	_	ns	1	
Body Diode Reverse Recovery Time	t _{RR}		21.1		ns		
Body Diode Reverse Recovery Charge	Q _{RR}		11.9	—	nC	I _F = 6A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.

Device mounted on FR-4 FCB, with minimum recommended pair ayout, single sided.
Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



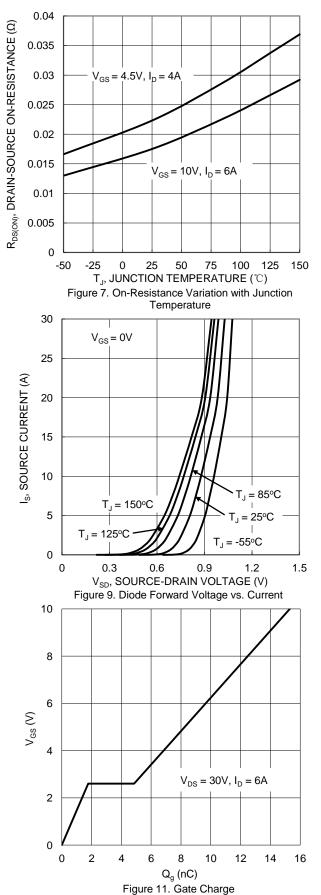
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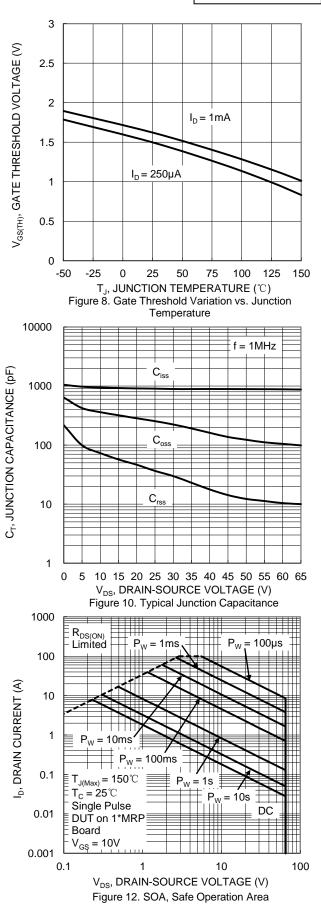


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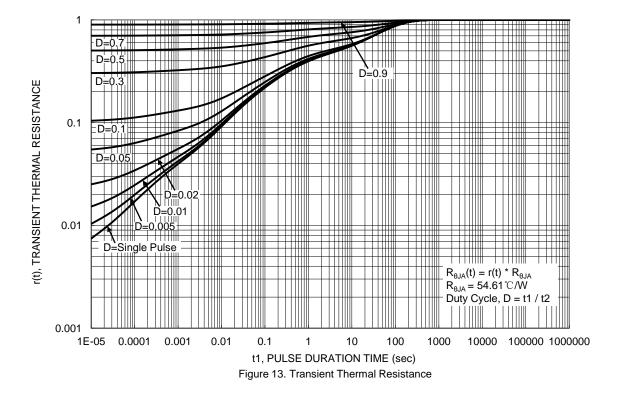






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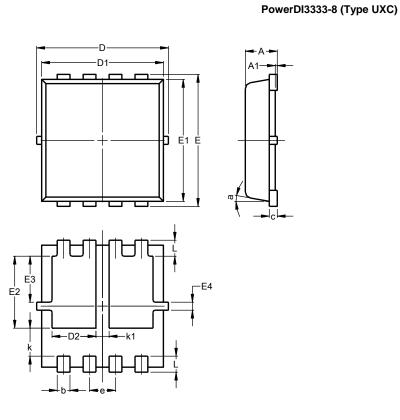






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

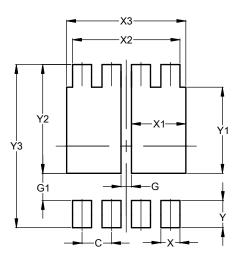


	PowerDI3333-8					
(Type UXC)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
e	_	_	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
a	0°	12°	10°			
All I	Dimens	sions ir	n mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.600
Х	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600



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